

Silicon PNP Power Transistors

2SA1008

DESCRIPTION

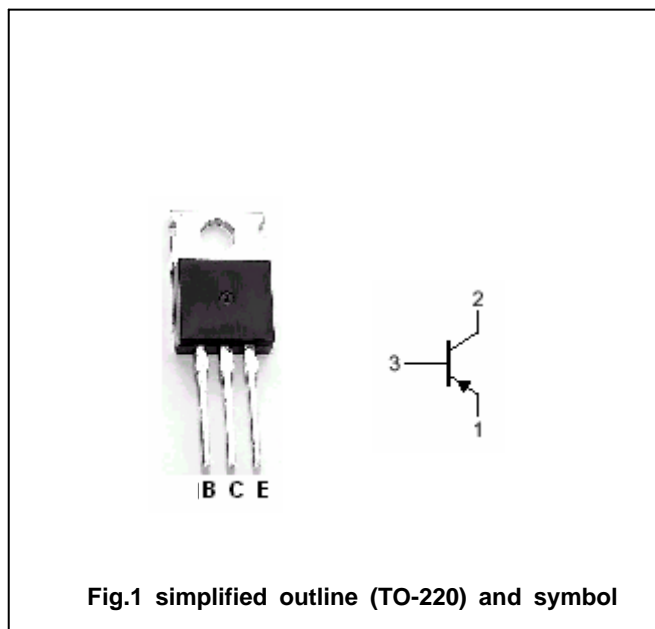
- With TO-220 package
- Complement to type 2SC2331
- Low collector saturation voltage
- Fast switching speed

APPLICATIONS

- Switching regulators
- DC/DC converters
- High frequency power amplifiers

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-2.0	A
I_{CM}	Collector current-Peak		-4.0	A
I_B	Base current		-1.0	A
P_T	Total power dissipation	$T_a=25$	1.5	W
		$T_C=25$	15	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

Silicon PNP Power Transistors

2SA1008

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-1.0A, I _B =-0.1A, L=1mH	-100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A; I _B =-0.1A			-0.6	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1A; I _B =-0.1A			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-10	μA
h _{FE-1}	DC current gain	I _C =-0.1A; V _{CE} =-5V	40			
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-5V	40		200	

Switching times resistive load

t _{on}	Turn-on time	I _C =-1.0A I _{B1} =- I _{B2} =-0.1A R _L =50 ; V _{CC} 50V			0.5	μs
t _s	Storage time				1.5	μs
t _f	Fall time				0.5	μs

◆ h_{FE-2} Classifications

M	L	K
40-80	60-120	100-200

Silicon PNP Power Transistors

2SA1008

PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)

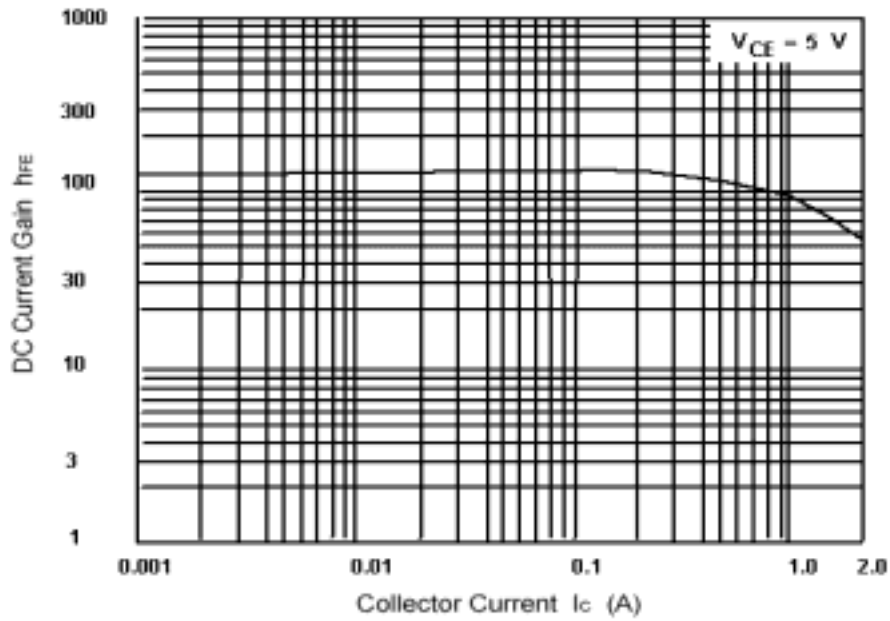


Fig.3 DC current Gain

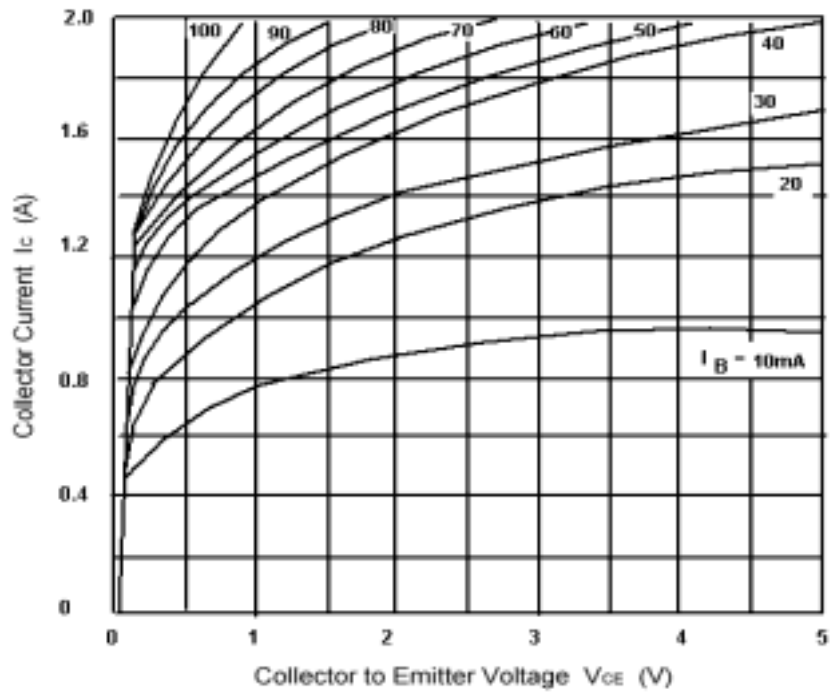


Fig.4 Static Characteristic

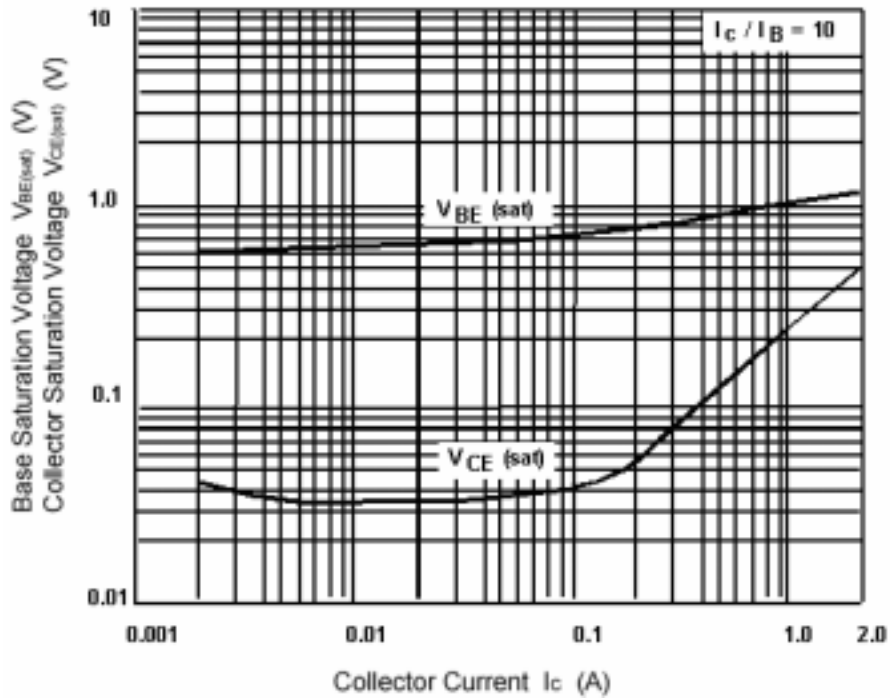


Fig.5 Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

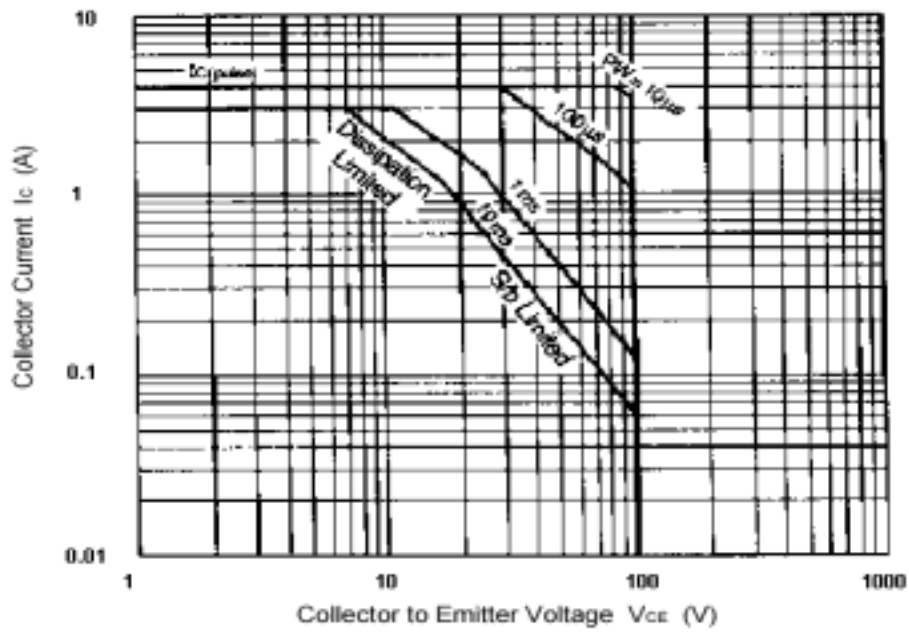


Fig.6 Safe Operating Area